

DATA SHEET

BUX84; BUX85 Silicon diffused power transistors

Product specification
Supersedes data of February 1996
File under Discrete Semiconductors, SC06

1997 Aug 13

Silicon diffused power transistors

BUX84; BUX85

DESCRIPTION

High-voltage, high-speed, glass-passivated NPN power transistor in a TO-220AB package.

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems
- Switching applications.

PINNING

PIN	DESCRIPTION
1	base
2	collector; connected to mounting base
3	emitter

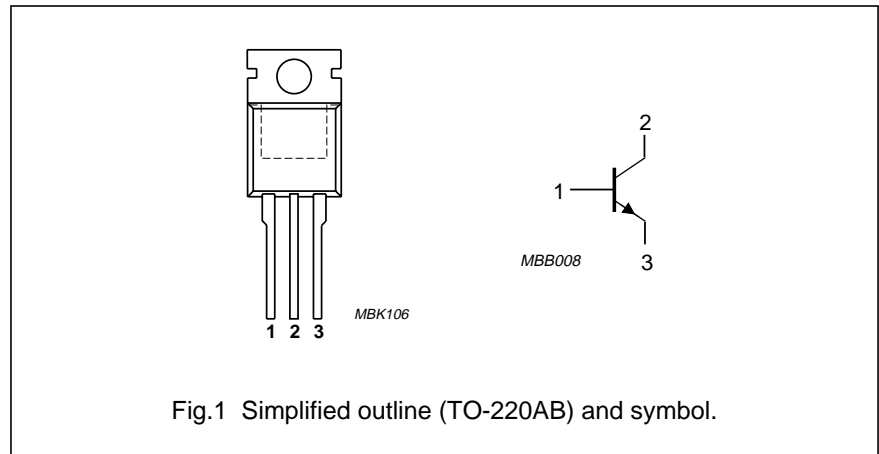


Fig.1 Simplified outline (TO-220AB) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0	-	800	V
	BUX84				
V _{CEO}	collector-emitter voltage	open base	-	400	V
	BUX85				
V _{CEsat}	collector-emitter saturation voltage	I _C = 1 A; I _B = 200 mA; see Fig.7	-	1	V
I _C	collector current (DC)	see Figs 4 and 5	-	2	A
I _{CM}	collector current (peak value)	see Figs 4 and 5	-	3	A
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; see Fig.8	-	40	W
t _f	fall time	resistive load; see Fig.11	0.4	-	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-mb}	thermal resistance from junction to mounting base	2.5	K/W
R _{th j-a}	thermal resistance from junction to ambient in free air	70	K/W

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0$	–	800	V
	BUX84			1000	V
V_{CEO}	collector-emitter voltage	open base	–	400	V
	BUX84			450	V
I_C	collector current (DC)	see Figs 4 and 5	–	2	A
I_{CM}	collector current (peak value)	$t_p = 2$ ms; see Figs 4 and 5	–	3	A
I_B	base current (DC)		–	0.75	A
I_{BM}	base current (peak value)		–	1	A
I_{BM}	base current (reversed; peak value)	turn-off current	–	–1	A
P_{tot}	total power dissipation	$T_{mb} \leq 25$ °C; see Fig.8	–	40	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CEOsust}$	collector-emitter sustaining voltage	$I_C = 100$ mA; $I_{Boff} = 0$; $L = 25$ mH; see Figs 2 and 3	400	–	–	V
	BUX84		450	–	–	V
V_{CEsat}	collector-emitter saturation voltage	$I_C = 0.3$ A; $I_B = 30$ mA; see Fig.7	–	–	0.8	V
		$I_C = 1$ A; $I_B = 200$ mA; see Fig.7	–	–	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 1$ A; $I_B = 200$ mA; see Fig.9	–	–	1.1	V
I_{CES}	collector-emitter cut-off current	$V_{CEM} = V_{CEMSmax}$; $V_{BE} = 0$; note 1	–	–	200	μ A
		$V_{CEM} = V_{CEMSmax}$; $V_{BE} = 0$; $T_j = 125$ °C; note 1	–	–	1.5	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5$ V; $I_C = 0$	–	–	1	mA
h_{FE}	DC current gain	$V_{CE} = 5$ V; $I_C = 5$ A; see Fig.10	15	–	–	
		$V_{CE} = 5$ V; $I_C = 100$ mA; see Fig.10	20	50	100	
f_T	transition frequency	$V_{CE} = 10$ V; $I_C = 200$ mA; $f = 1$ MHz	–	20	–	MHz

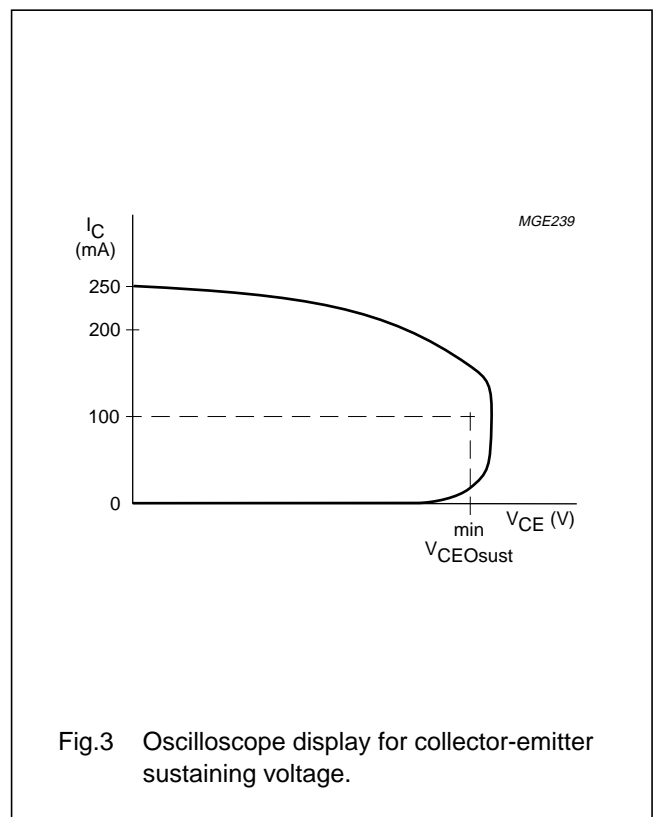
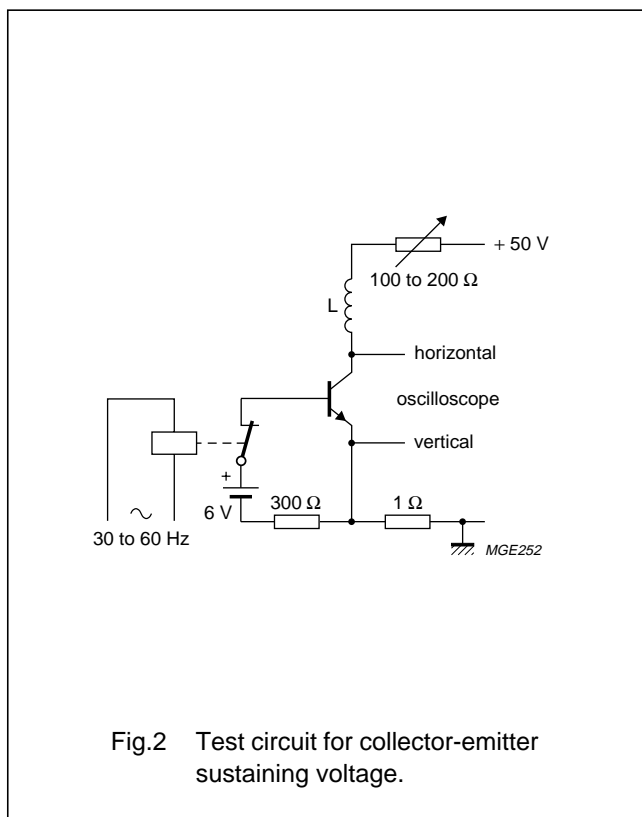
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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Switching times in horizontal deflection circuit (see Fig.11)						
t_{on}	turn-on time	$I_{Con} = 1\text{ A}; I_{Bon} = 200\text{ mA}; I_{Boff} = -400\text{ mA}; V_{CC} = 250\text{ V}$	–	0.2	0.5	μs
t_f	fall time	$I_{Con} = 1\text{ A}; I_{Bon} = 200\text{ mA}; I_{Boff} = -400\text{ mA}; V_{CC} = 250\text{ V}$	–	0.4	–	μs
		$I_{Con} = 1\text{ A}; I_{Bon} = 200\text{ mA}; I_{Boff} = -400\text{ mA}; V_{CC} = 250\text{ V}; T_{mb} = 95\text{ }^\circ\text{C}$	–	–	1.4	μs
t_s	storage time	$I_{Con} = 1\text{ A}; I_{Bon} = 200\text{ mA}; I_{Boff} = -400\text{ mA}; V_{CC} = 250\text{ V}$	–	2	3.5	μs

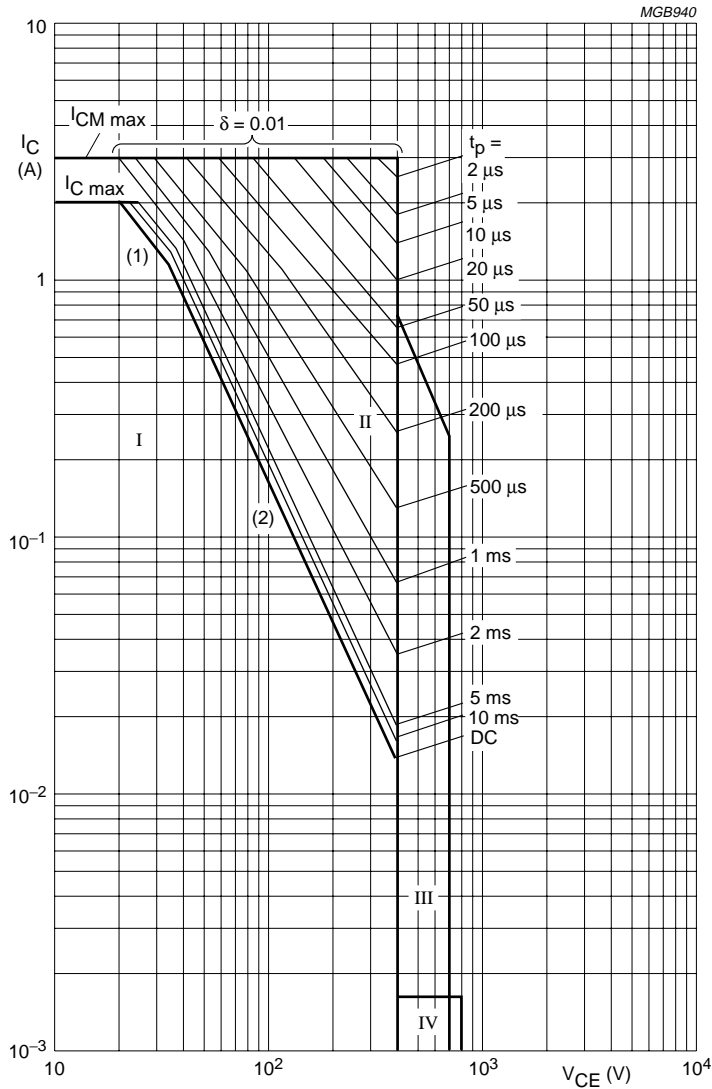
Note

1. Measured with a half-sinewave voltage (curve tracer).



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BUX84.

$T_{mb} \leq 50\ ^\circ C$.

I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

III - Area of permissible operation during turn-on in single transistor converters, provided $R_{BE} \leq 100\ \Omega$ and $t_p \leq 0.6\ \mu s$.

IV - Repetitive pulse operation in this region is permissible provided $V_{BE} \leq 0$ and $t_p \leq 2\ ms$.

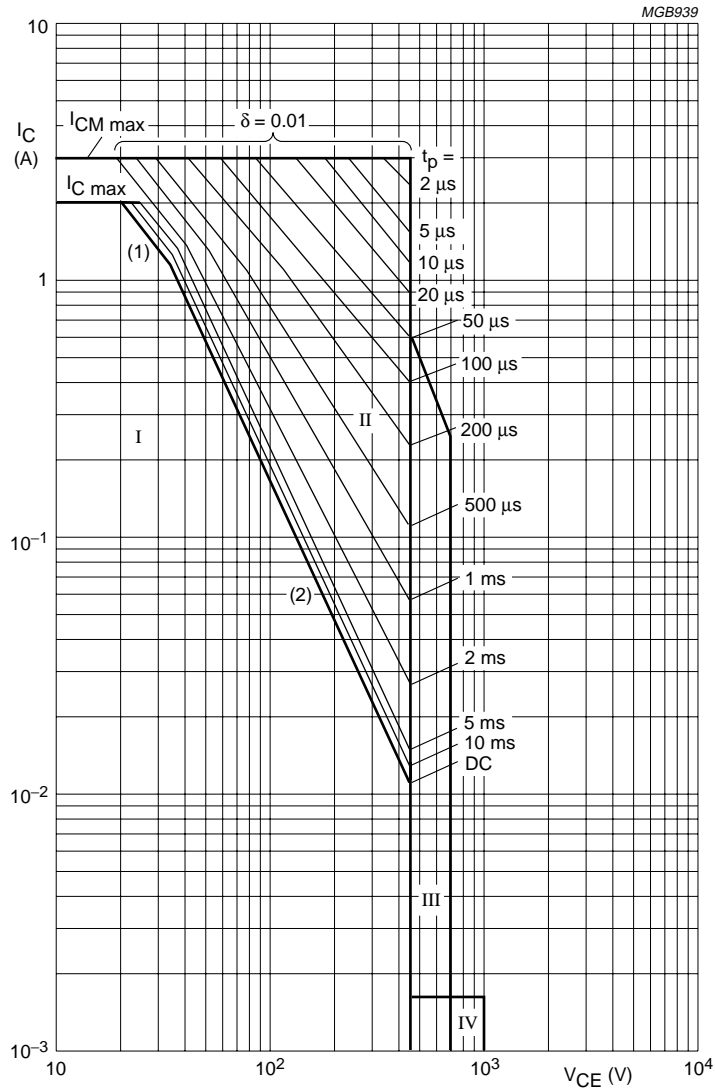
(1) $P_{tot\ max}$ and $P_{tot\ peak\ max}$ lines.

(2) Second breakdown limits.

Fig.4 Forward bias SOAR.

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BUX85.

$T_{mb} \leq 50 \text{ }^\circ\text{C}.$

I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

III - Area of permissible operation during turn-on in single transistor converters, provided $R_{BE} \leq 100 \text{ } \Omega$ and $t_p \leq 0.6 \text{ } \mu\text{s}.$

IV - Repetitive pulse operation in this region is permissible provided $V_{BE} \leq 0$ and $t_p \leq 2 \text{ ms}.$

(1) $P_{tot \text{ max}}$ and $P_{tot \text{ peak max}}$ lines.

(2) Second breakdown limits.

Fig.5 Forward bias SOAR.

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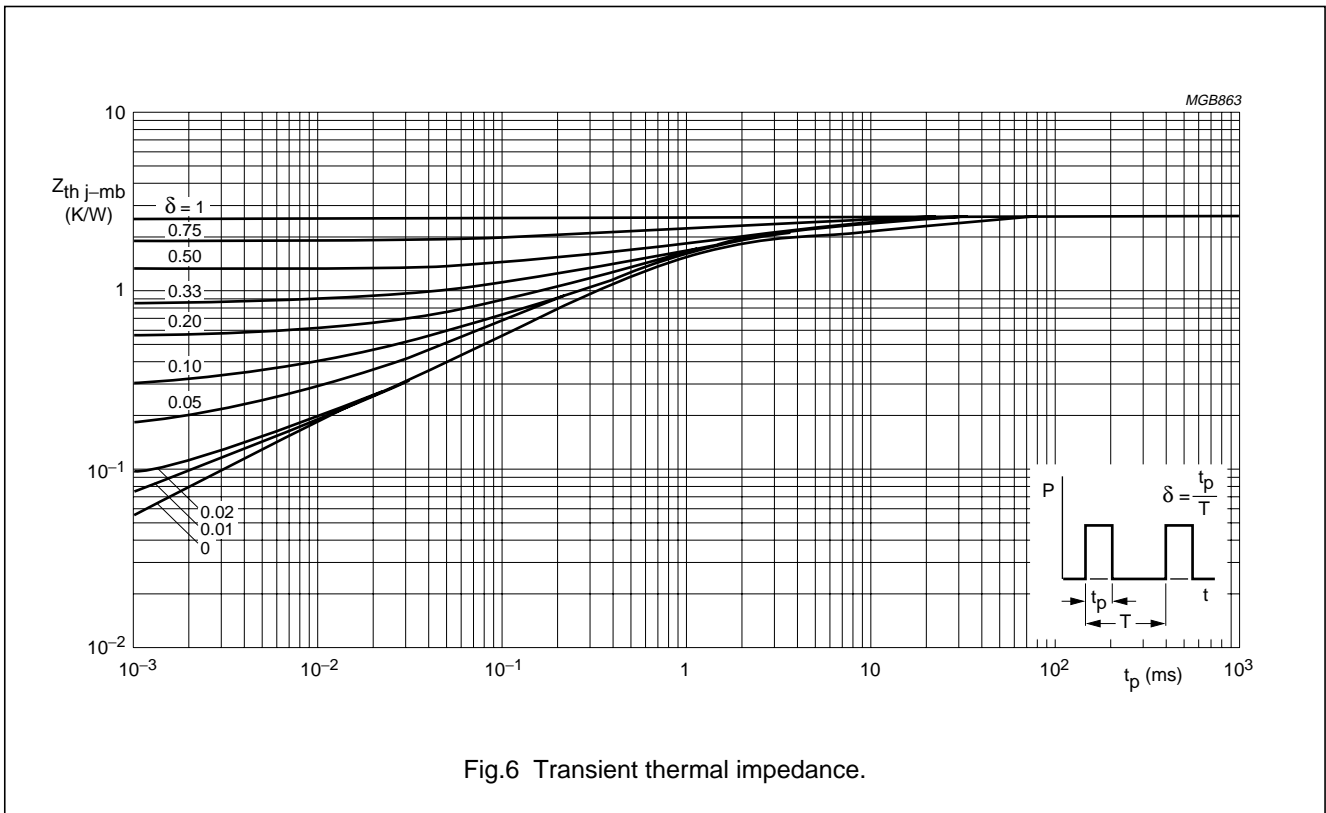
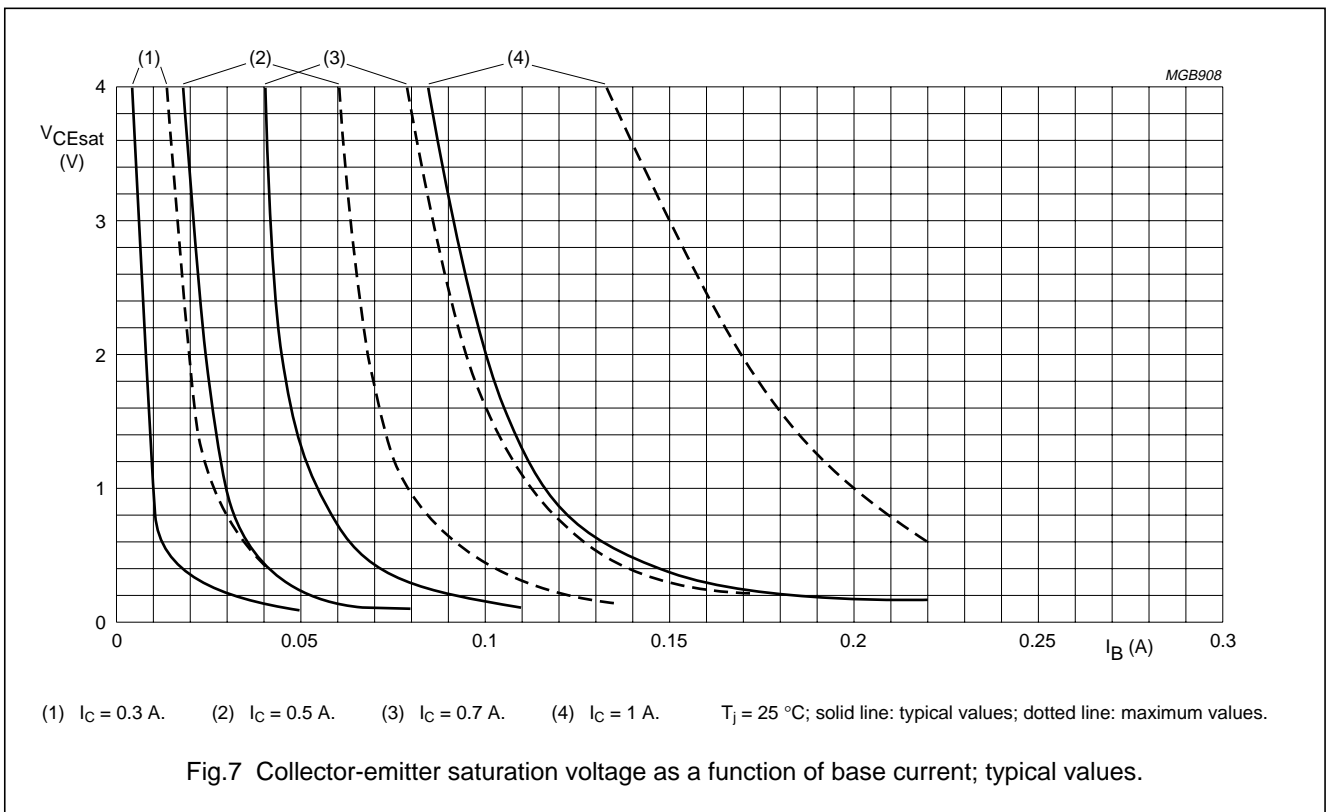


Fig.6 Transient thermal impedance.

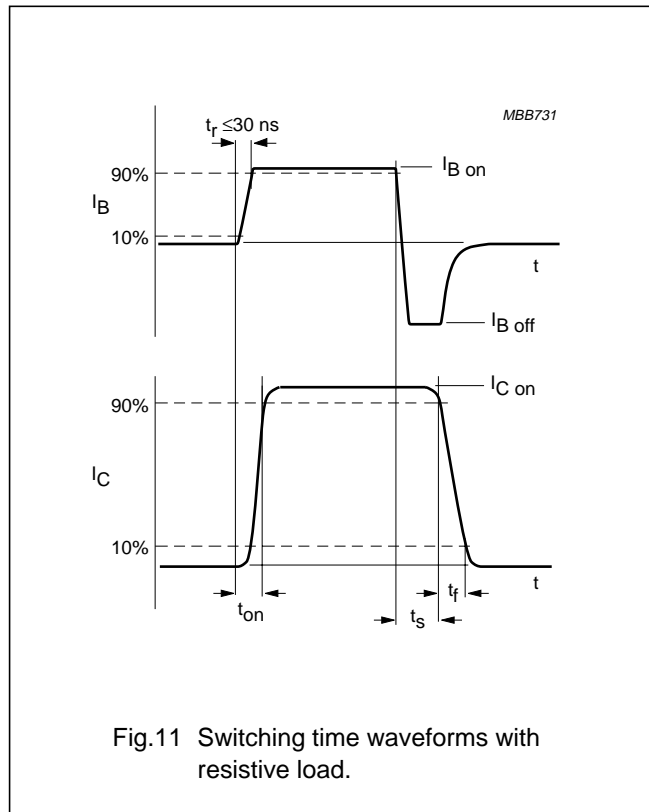
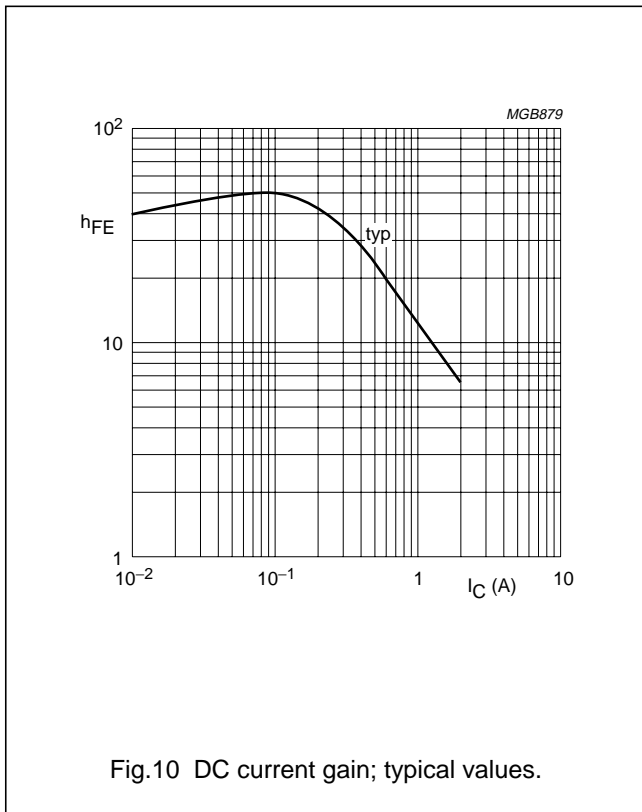
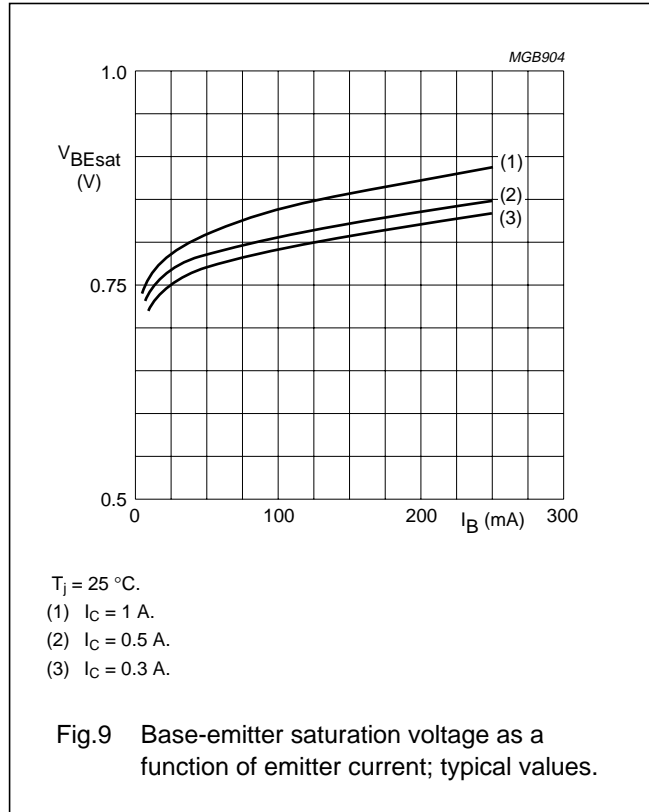
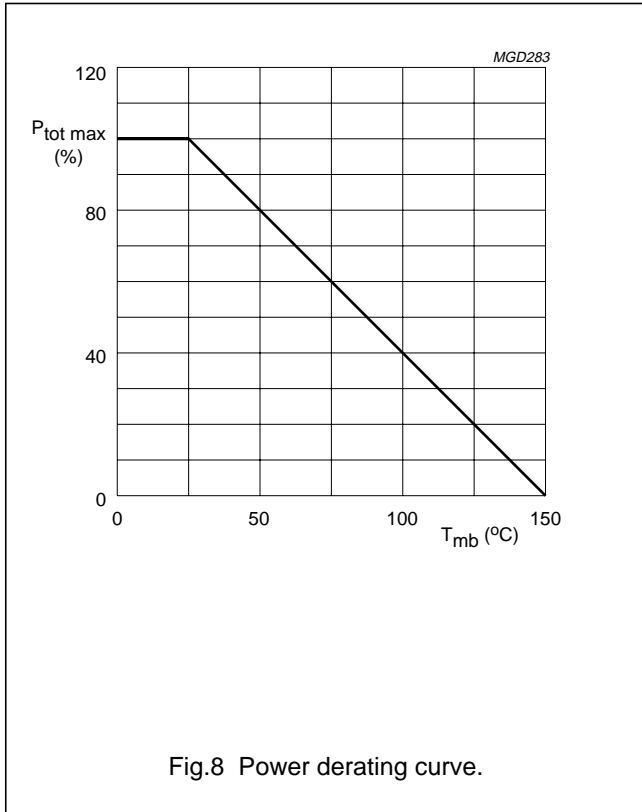


(1) $I_C = 0.3\text{ A}$. (2) $I_C = 0.5\text{ A}$. (3) $I_C = 0.7\text{ A}$. (4) $I_C = 1\text{ A}$. $T_j = 25\text{ }^\circ\text{C}$; solid line: typical values; dotted line: maximum values.

Fig.7 Collector-emitter saturation voltage as a function of base current; typical values.

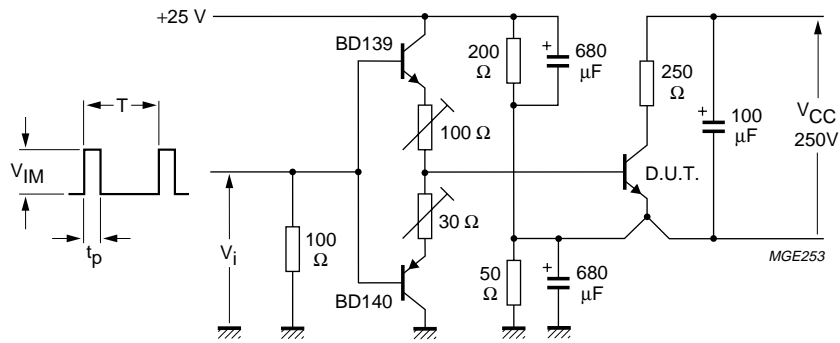
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$t_p = 20 \mu s$; $T = 2 ms$; $V_{IM} = 15 V$.

Fig.12 Test circuit resistive load.

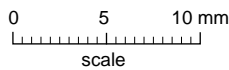
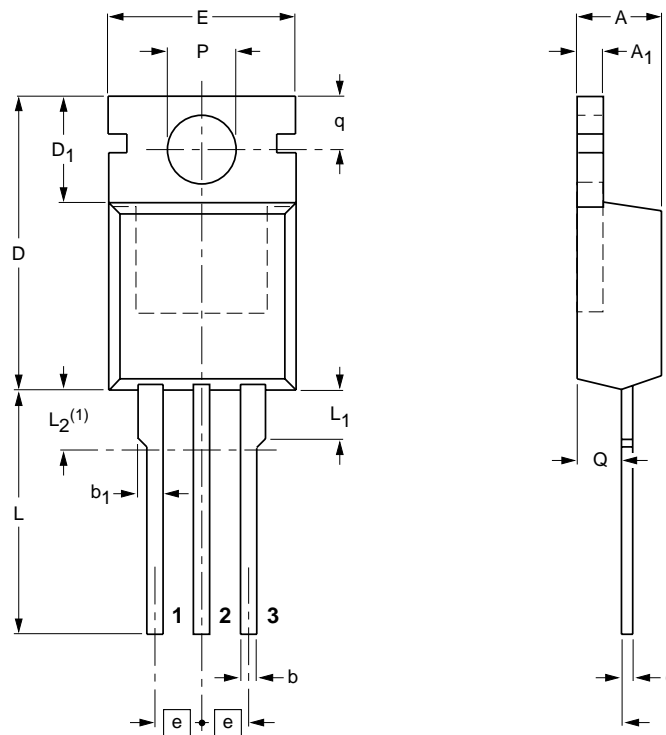
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PACKAGE OUTLINE

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	c	D	D ₁	E	e	L	L ₁	L ₂ ⁽¹⁾ max.	P	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.7	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

Note

1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT78		TO-220AB				97-06-11

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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